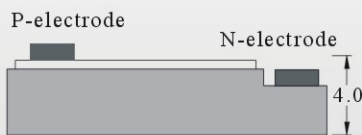




Product Introduction

LPABG23A



Unit: mil

LPABG23A

Mechanical Specifications

Size:
 Chip Size: 10mil x 23mil
 (260±20µm x 590±20µm)
 Chip Thickness: 4mil(100±10µm)
 Pad Size: 2.9mil(72±10µm)

Pad Metal
 P Electrode: Au
 N Electrode: Au

Typical Electrical/Optical Characteristics:

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _f	I _f =20mA	2.8	---	3.6	V
Reverse Current	I _r	V _r =5V	---	---	1	µA
Dominant Wavelength	λ _d	I _f =20mA	445	---	475	nm
Spectra Half-width	Δλ	I _f =20mA	---	---	30	nm
Luminous Power	P _o	I _f =20mA	24.5	---	33	mW

Parameters range:

Po(mW) \ Wd(nm)	447.5-450	450-452.5	452.5-455	455-457.5	457.5-460	460-462.5
31-33	FBPX	GAPX	GBPX	HAPX	HBPX	IAPX
29-31	FBOX	GAOX	GBOX	HAOX	HBOX	IAOX
27.5-29	FBNX	GANX	GBNX	HANX	HBNX	IANX
26-27.5	FBMX	GAMX	GBMX	HAMX	HBMX	IAMX
24.5-26	FBLX	GALX	GBLX	HALX	HBLX	IALX

Notes:

- The Electrical/Optical Characteristics are measured with LatticePower electro-optical equipment at (T_a=25°C) without an encapsulant.
- GaN LED chip is an electrostatic sensitive product, so ESD protection during chip handling is recommended.
- We welcome customer's enquiry for special requirements.